INTEGRATED CIRCUITS

DATA SHEET

74LVC11Triple 3-input AND gate

Product specification Supersedes data of 1998 Apr 28 2004 Jan 13





Triple 3-input AND gate

74LVC11

FEATURES

• Wide supply voltage range from 1.2 to 3.6 V

• Inputs accept voltages up to 5.5 V

• CMOS low power consumption

· Direct interface with TTL levels

· Output capability: standard

· I_{CC} category: SSI

• In accordance with JEDEC standard no. 8-1A

ESD protection:

HBM EIA/JESD22-A114-A exceeds 2000 V MM EIA/JESD22-A115-A exceeds 200 V.

DESCRIPTION

The 74LVC11 is a high-performance, low power, low-voltage, Si-gate CMOS device and superior to most advanced CMOS compatible TTL families.

The 74LVC11 provides the 3-input AND function.

QUICK REFERENCE DATA

GND = 0 V; $T_{amb} = 25 \, ^{\circ}C$; $t_r = t_f \le 2.5 \, \text{ns}$.

SYMBOL PARAMETER t _{PHL} /t _{PLH} propagation delay nA, nB, nC to nY C _I input capacitance	CONDITIONS	TYPICAL	UNIT	
t _{PHL} /t _{PLH}	propagation delay nA, nB, nC to nY	$C_L = 50 \text{ pF}; V_{CC} = 3.3 \text{ V}$	3.7	ns
Cı	input capacitance		5.0	pF
C _{PD}	power dissipation capacitance per gate	notes 1 and 2	26	pF

Notes

1. C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

 $P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma (C_L \times V_{CC}^2 \times f_o)$ where:

 f_i = input frequency in MHz;

 f_0 = output frequency in MHz;

C_L = output load capacitance in pF;

V_{CC} = supply voltage in Volts;

N = total switching outputs;

 $\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of the outputs.

2. The condition is $V_I = GND$ to V_{CC} .

ORDERING INFORMATION

TYPE NUMBER	TEMPERATURE RANGE		PACKAGE				
I I PE NOWBER	TEMPERATURE RANGE	PINS	PACKAGE	MATERIAL	CODE		
74LVC11D	–40 to +85 °C	14	SO14	plastic	SOT108-1		
74LVC11DB	-40 to +85 °C	14	SSOP14	plastic	SOT337-1		
74LVC11PW	–40 to +85 °C	14	TSSOP14	plastic	SOT402-1		
74LVC11BQ	-40 to +85 °C	14	DHVQFN14	plastic	SOT762-1		

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FUNCTION TABLE

See note 1.

	INPUT	OUTPUT	
nA	nB	nC	nY
L	L	L	L
L	L	H	L
L	Н	L	L
L	Н	Н	L
Н	L	L	L
Н	L	H	L
Н	Н	L	L
Н	Н	Н	Н

Note

L = LOW voltage level.

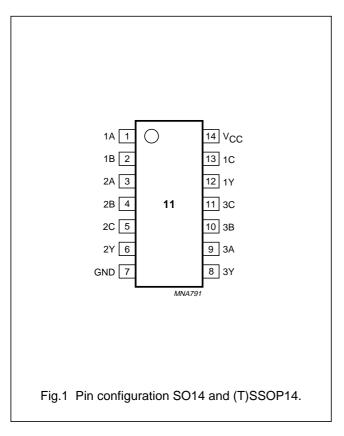
PINNING

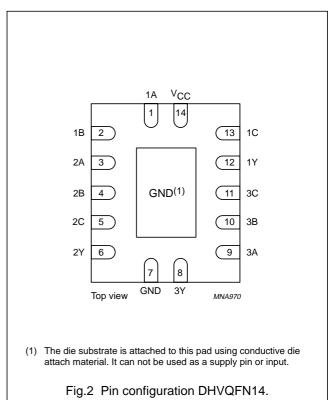
PIN	SYMBOL	DESCRIPTION
1	1A	data input
2	1B	data input
3	2A	data input
4	2B	data input
5	2C	data input
6	2Y	data output
7	GND	ground (0 V)
8	3Y	data output
9	3A	data input
10	3B	data input
11	3C	data input
12	1Y	data output
13	1C	data input
14	V _{CC}	positive supply voltage

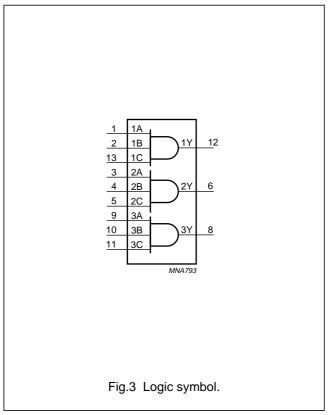
^{1.} H = HIGH voltage level.

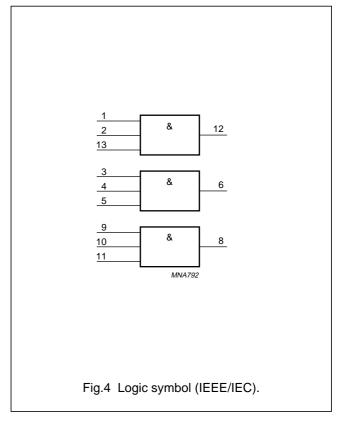
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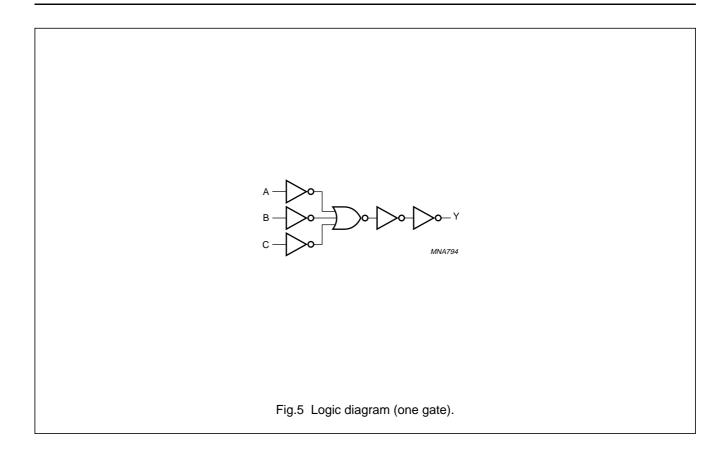






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RECOMMENDED OPERATING CONDITIONS

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CC}	supply voltage	for maximum speed performance	2.7	3.6	V
		for low-voltage applications	1.2	3.6	V
VI	input voltage		0	5.5	V
Vo	output voltage		0	V _{CC}	V
T _{amb}	operating ambient temperature		-40	+85	°C
t _r , t _f	input rise and fall times	V _{CC} = 1.2 to 2.7 V	0	20	ns/V
		V _{CC} = 2.7 to 3.6 V	0	10	ns/V

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134); voltages are referenced to GND (ground = 0 V).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CC}	supply voltage		-0.5	+6.5	V
I _{IK}	input diode current	V _I < 0	_	-50	mA
VI	input voltage	note 1	-0.5	+6.5	V
I _{OK}	output diode current	$V_O > V_{CC}$ or $V_O < 0$	_	±50	mA
Vo	output voltage	note 1	-0.5	V _{CC} + 0.5	V
Io	output source or sink current	$V_{O} = 0$ to V_{CC}	_	±50	mA
I _{GND} , I _{CC}	V _{CC} or GND current		_	±100	mA
T _{stg}	storage temperature range		-65	+150	°C
P _{tot}	power dissipation	$T_{amb} = -40 \text{ to } +125 \text{ °C}; \text{ note } 2$	_	500	mW

Notes

- 1. The input and output voltage ratings may be exceeded if the input and output current ratings are observed.
- 2. For SO14 packages: above 70 °C the value of P_D derates linearly with 8 mW/K.
 - For (T)SSOP14 packages: above 60 $^{\circ}$ C the value of P_D derates linearly with 5.5 mW/K.

For DHVQFN14 packages: above 60 °C the value of P_D derates linearly with 4.5 mW/K.

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DC CHARACTERISTICS

At recommended operating conditions voltages are referenced to GND (ground = 0 V).

OVMBOL	DADAMETED	TEST COND	TIONS	54151	TVD (1)	BAA W		
SYMBOL	PARAMETER	OTHER V _C		MIN.	TYP. ⁽¹⁾	MAX.	UNIT	
T _{amb} = -40) °C to +85 °C	•	•	•			•	
V _{IH}	HIGH level input voltage		1.2	V _{CC}	_	_	V	
			2.7 to 3.6	2.0	_	_	V	
V _{IL}	LOW-level input voltage		1.2	_	_	GND	V	
			2.7 to 3.6	_	_	0.8	V	
V _{OH}	HIGH-level output voltage	$V_I = V_{IH}$ or V_{IL}						
		$I_0 = -12 \text{ mA}$	2.7	V _{CC} – 0.5	_	_	V	
		$I_{O} = -100 \mu\text{A}$	3.0	V _{CC} – 0.2	V _{CC}	_	V	
		$I_0 = -12 \text{ mA}$	3.0	V _{CC} – 0.6		_	V	
		$I_0 = -24 \text{ mA}$	3.0	V _{CC} – 1.0	_	_	V	
V _{OL}	LOW-level output voltage	$V_I = V_{IH}$ or V_{IL}						
		I _O = 12 mA	2.7	_	_	0.40	V	
		I _O = 100 μA	3.0	_	GND	0.20	V	
		I _O = 24 mA	3.0	_	_	0.55	V	
ILI	input leakage current	$V_I = 5.5 \text{ V or GND}$	3.6	_	±0.1	±5	μΑ	
I _{CC}	quiescent supply current	$V_I = V_{CC}$ or GND; $I_O = 0$	3.6	-	0.1	10	μΑ	
ΔI_{CC}	additional quiescent supply current per input pin	$V_{I} = V_{CC} - 0.6 \text{ V};$ $I_{O} = 0$	2.7 to 3.6	-	5	500	μΑ	

Note

1. All typical values are measured at V_{CC} = 3.3 V and T_{amb} = 25 °C.

AC CHARACTERISTICS

GND = 0 V; t_{r} = $t_{f} \leq$ 2.5 ns; C_{L} = 50 pF; R_{L} = 500 $\Omega.$

SYMBOL	PARAMETER	TEST CONDIT	TIONS	MIN.	TYP. ⁽¹⁾	MAX.	UNIT
STIVIBUL	PARAMETER	WAVEFORMS	V _{CC} (V)	IVIIIN.		WAA.	UNIT
T _{amb} = -40 to +85 °C		•					
t _{PHL} /t _{PLH}	propagation delay	see Figs 6 and 7	2.7	_	_	7.0	ns
			3.0 to 3.6	_	3.7	6.2	ns

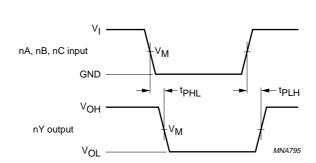
Note

1. Typical value is measured at V_{CC} = 3.3 V and T_{amb} = 25 °C.

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AC WAVEFORMS

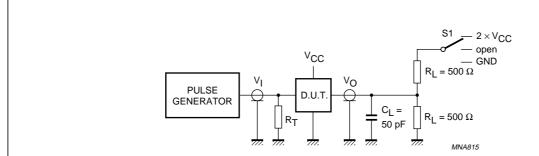


 V_M = 1.5 V at $V_{CC} \ge 2.7$ V.

 V_{M} = 0.5V $_{CC}$ at V_{CC} < 2.7 V.

 V_{OL} and V_{OH} are the typical output voltage drop that occur with the output load.

Fig.6 Input (nA, nB and nC) to output (nY) propagation delays.



SWITCH POSITION TEST S1 tput/tput open	POSITION
TEST	S1
t _{PLH} /t _{PHL}	open

V _{CC}	VI
<2.7 V	V _{CC}
2.7 to 3.6 V	2.7 V

Definitions for test circuit:

 R_L = load resistor.

 C_L = load capacitance including jig and probe capacitance.

 R_T = termination resistance should be equal to the output impedance Z_0 of the pulse generator.

Fig.7 Load circuitry for switching times.

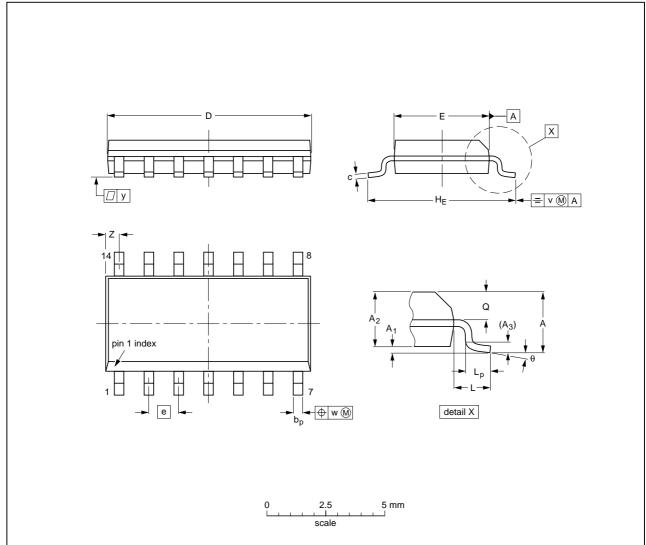
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PACKAGE OUTLINES

SO14: plastic small outline package; 14 leads; body width 3.9 mm

SOT108-1



DIMENSIONS (inch dimensions are derived from the original mm dimensions)

UNIT	A max.	A ₁	A ₂	Α3	bp	С	D ⁽¹⁾	E ⁽¹⁾	е	HE	L	Lp	Q	v	w	у	z ⁽¹⁾	θ
mm	1.75	0.25 0.10	1.45 1.25	0.25	0.49 0.36	0.25 0.19	8.75 8.55	4.0 3.8	1.27	6.2 5.8	1.05	1.0 0.4	0.7 0.6	0.25	0.25	0.1	0.7 0.3	8°
inches	0.069	0.010 0.004	0.057 0.049	0.01		0.0100 0.0075	0.35 0.34	0.16 0.15	0.05	0.244 0.228	0.041	0.039 0.016		0.01	0.01	0.004	0.028 0.012	0°

Note

1. Plastic or metal protrusions of 0.15 mm (0.006 inch) maximum per side are not included.

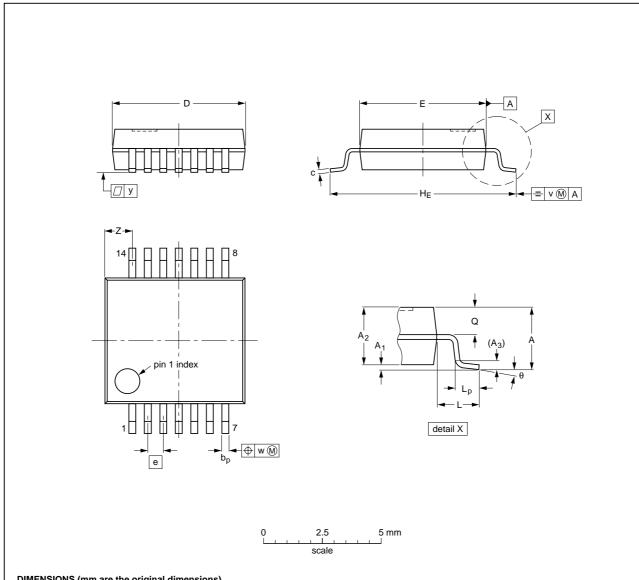
OUTLINE		REFER	ENCES	EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE
SOT108-1	076E06	MS-012			99-12-27 03-02-19

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SSOP14: plastic shrink small outline package; 14 leads; body width 5.3 mm

SOT337-1



DIMENSIONS (mm are the original dimensions)

UNIT	A max.	A ₁	A ₂	A ₃	bp	С	D ⁽¹⁾	E ⁽¹⁾	е	HE	L	Lp	ø	v	w	у	Z ⁽¹⁾	θ
mm	2	0.21 0.05	1.80 1.65	0.25	0.38 0.25	0.20 0.09	6.4 6.0	5.4 5.2	0.65	7.9 7.6	1.25	1.03 0.63	0.9 0.7	0.2	0.13	0.1	1.4 0.9	8° 0°

1. Plastic or metal protrusions of 0.25 mm maximum per side are not included.

OUTLINE		REFER	EUROPEAN	ISSUE DATE			
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE	
SOT337-1		MO-150				-99-12-27 03-02-19	

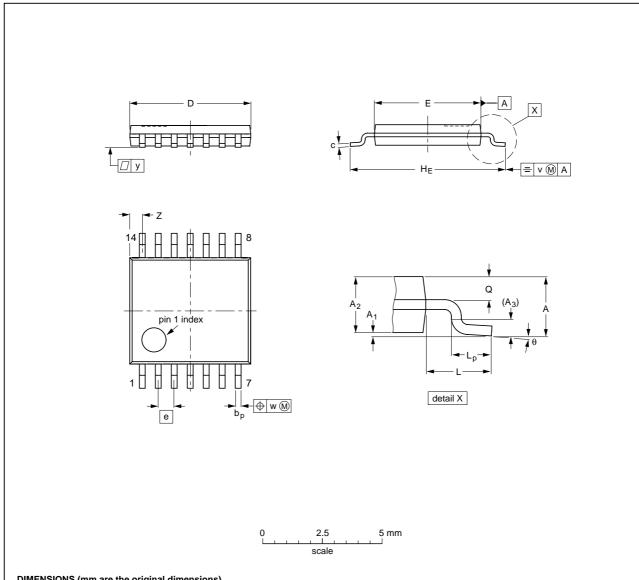
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TSSOP14: plastic thin shrink small outline package; 14 leads; body width 4.4 mm

SOT402-1



DIMENSIONS (mm are the original dimensions)

UNIT	A max.	A ₁	A ₂	A ₃	bp	С	D ⁽¹⁾	E ⁽²⁾	е	HE	L	Lp	ø	v	w	у	Z ⁽¹⁾	θ
mm	1.1	0.15 0.05	0.95 0.80	0.25	0.30 0.19	0.2 0.1	5.1 4.9	4.5 4.3	0.65	6.6 6.2	1	0.75 0.50	0.4 0.3	0.2	0.13	0.1	0.72 0.38	8° 0°

Notes

- 1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
- 2. Plastic interlead protrusions of 0.25 mm maximum per side are not included.

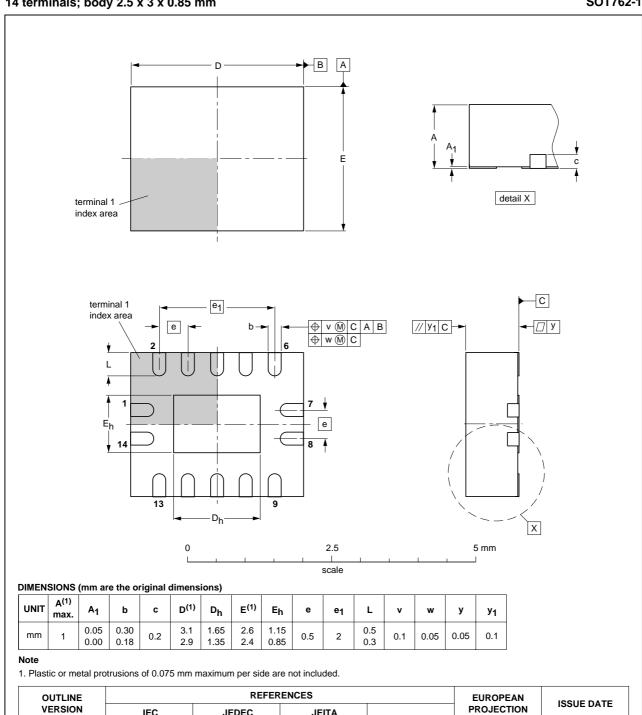
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VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE	
SOT402-1		MO-153				-99-12-27 03-02-18	

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DHVQFN14: plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 14 terminals; body 2.5 x 3 x 0.85 mm SOT762-1



OUTLINE		REFER	EUROPEAN	ISSUE DATE			
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE	
SOT762-1		MO-241				02-10-17 03-01-27	

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